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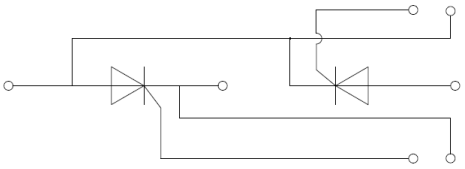

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				0	1

1

FIG.1:Power dissipation vs. on-state current (per thyristor or diode)

FIG.2: Maximum transient thermal impedance junction to case (per thyristor or diode)

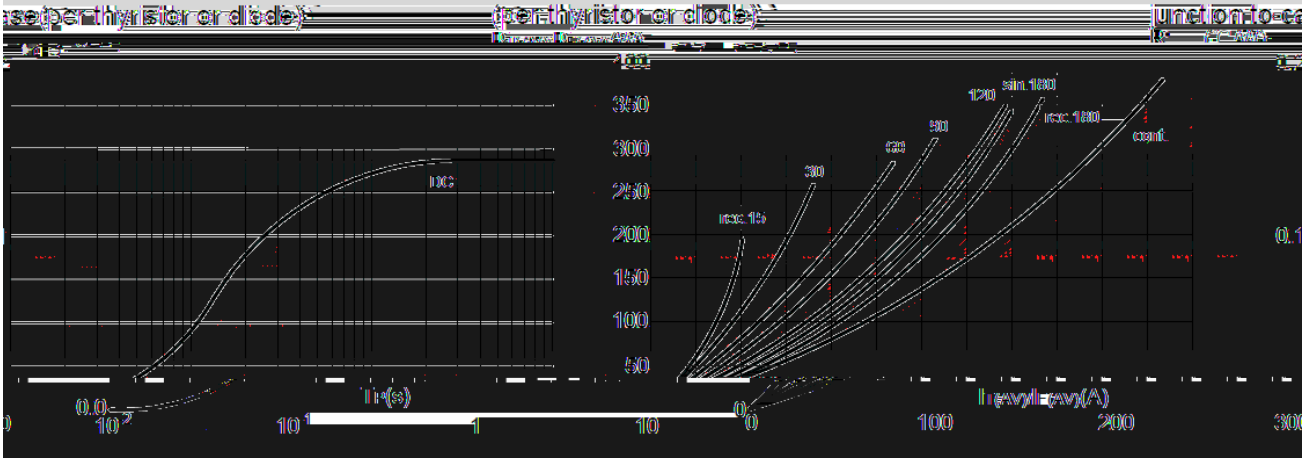


FIG.3: Forward characteristics (per thyristor or diode)

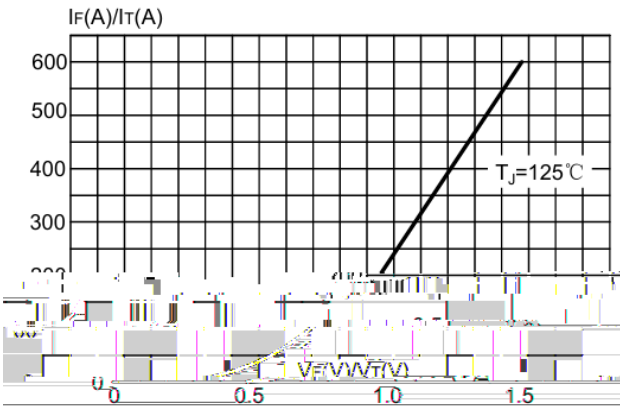


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

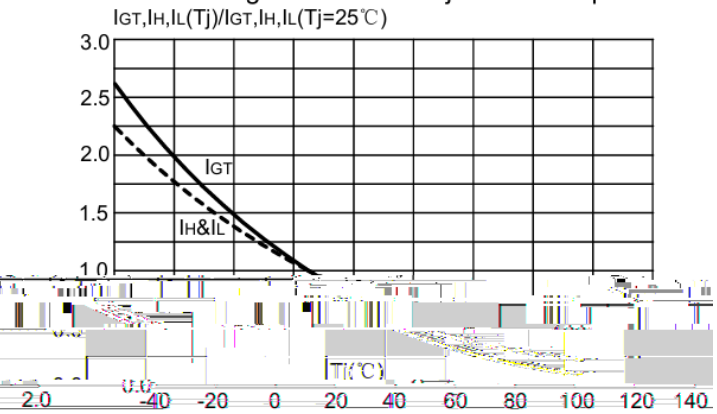


FIG.5 Gate trigger characteristics

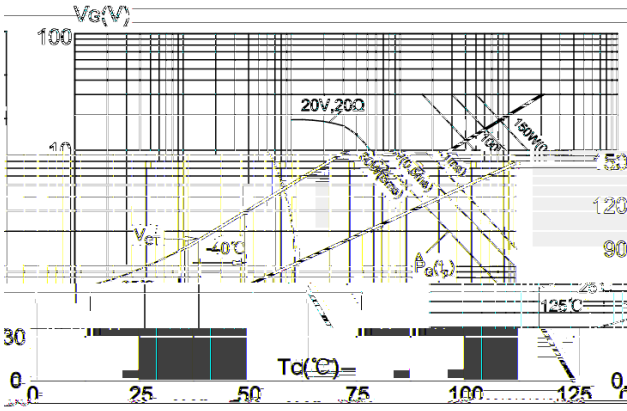
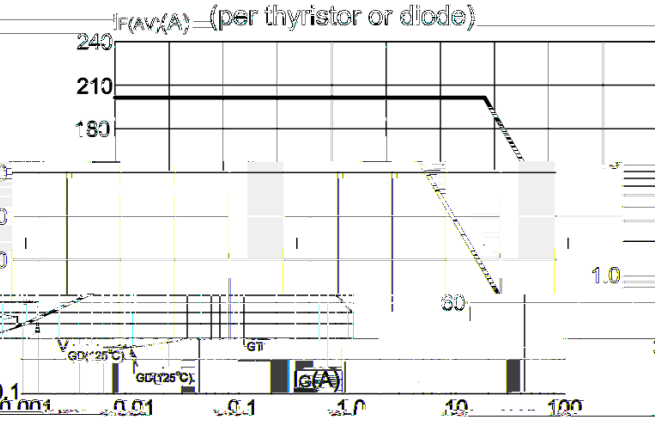


FIG.6: Forward current vs. case temperature (per thyristor or diode)



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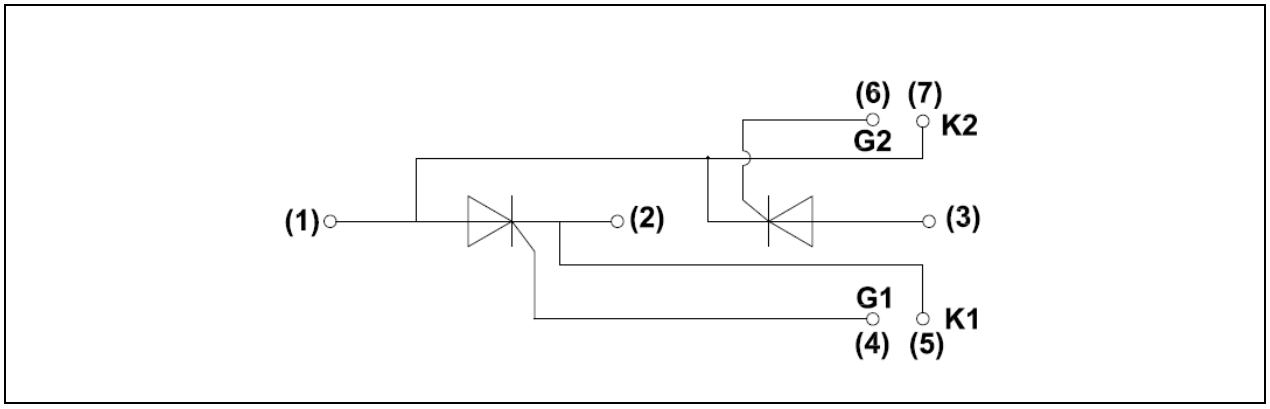
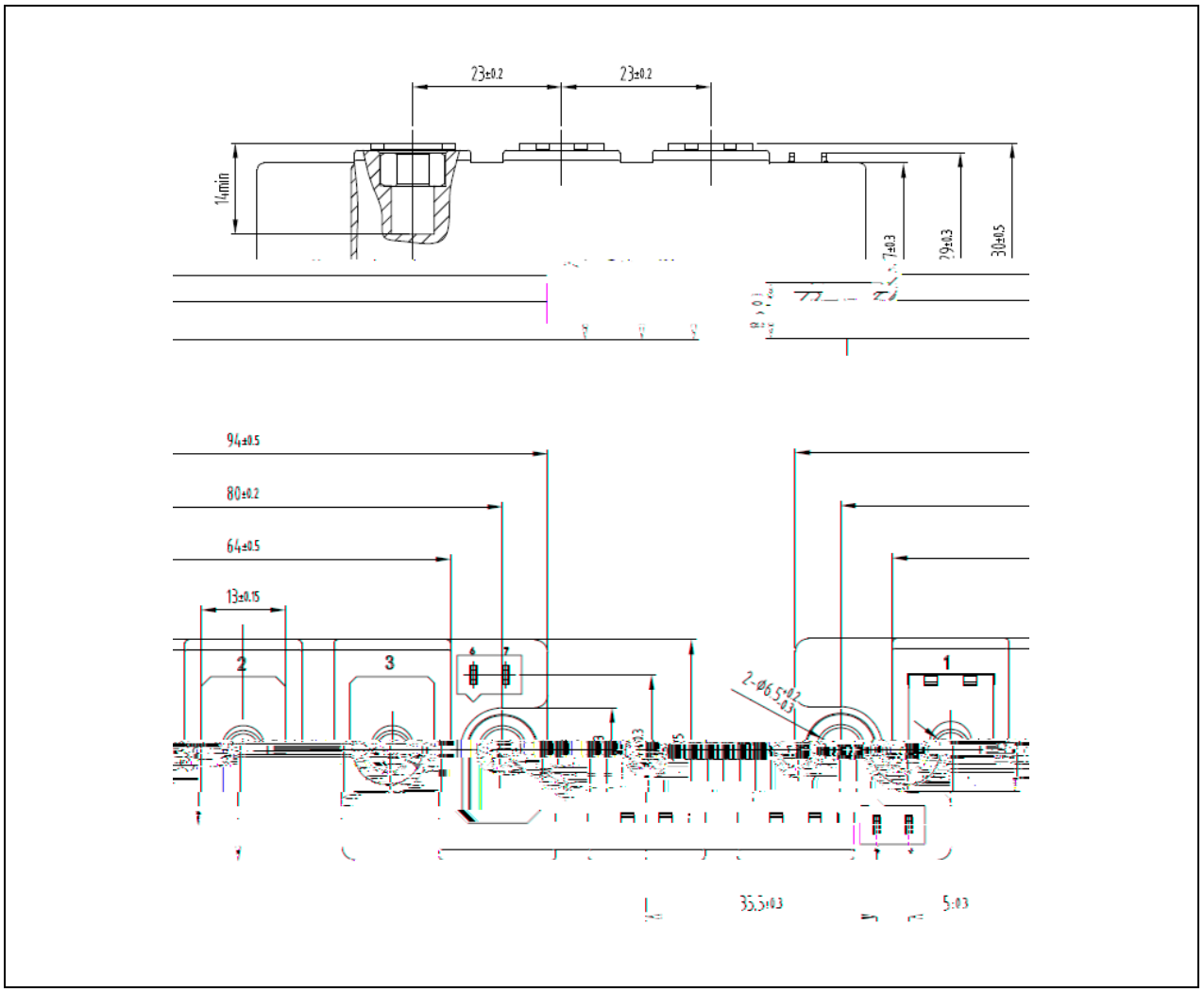

(6)
(7)
K2
G2
(1)
(2)
(3)
G1
K1
(4)
(5)


23±0.2
23±0.2
14min
7±0.3
29±0.3
30±0.5
94±0.5
80±0.2
64±0.5
13±0.15
2
3
1
35.5±0.3
5±0.3